



FIG. 1

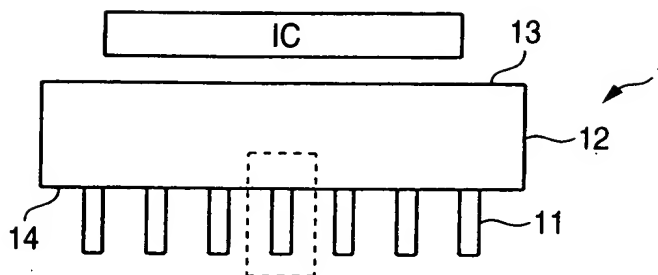


FIG. 2

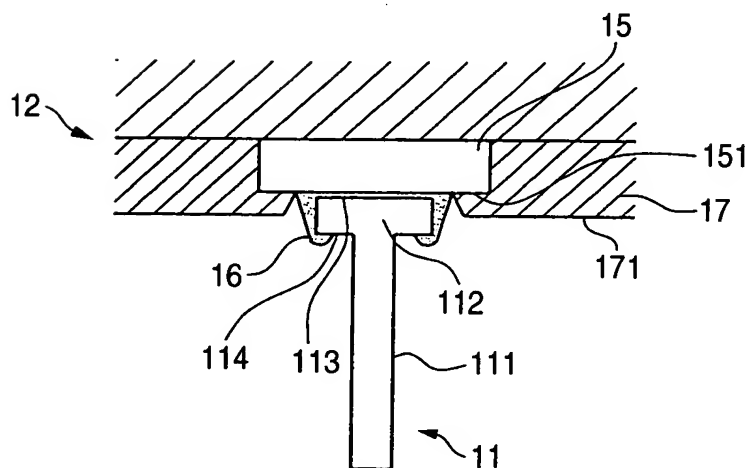
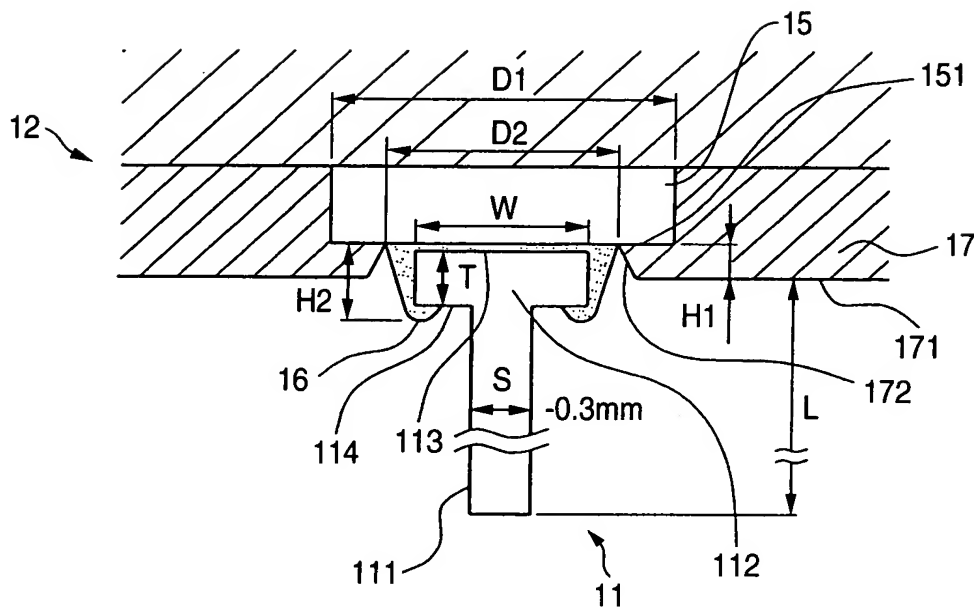


FIG. 3



A cross-sectional view of a semiconductor device 12. The device includes a substrate 15 with a top layer 151. A central structure 11 is formed on the substrate, consisting of a base 111 and a top layer 112. The structure 11 is surrounded by a material 16 and a layer 17 with a pattern 171. The device is shown in a cross-sectional view with various layers and structures labeled with reference numerals.

[illegible]

FIG. 5

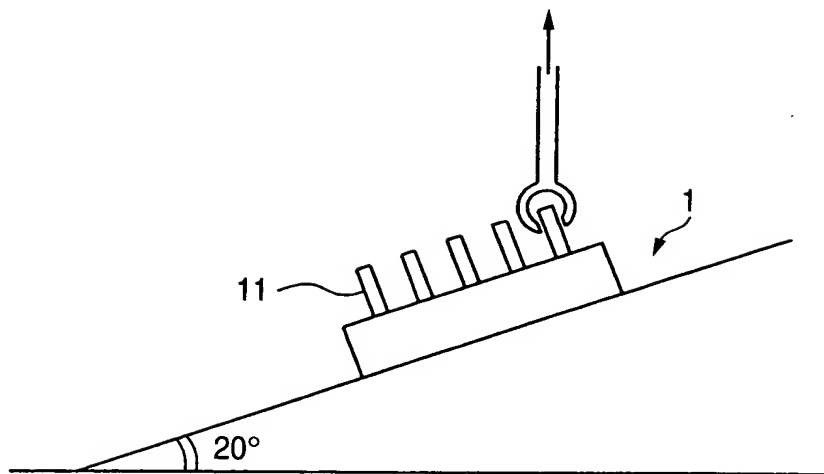


FIG. 6A

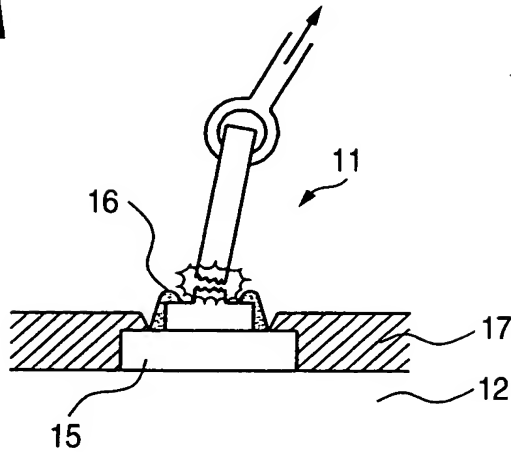


FIG. 6B

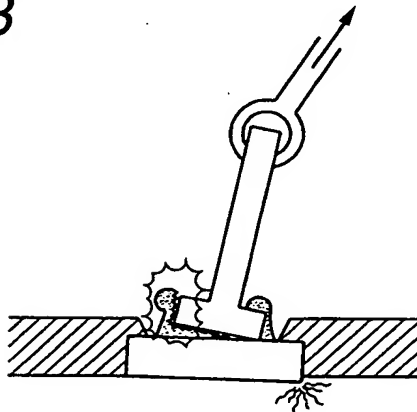


FIG. 6C

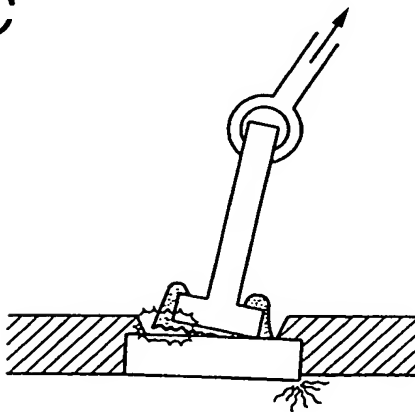
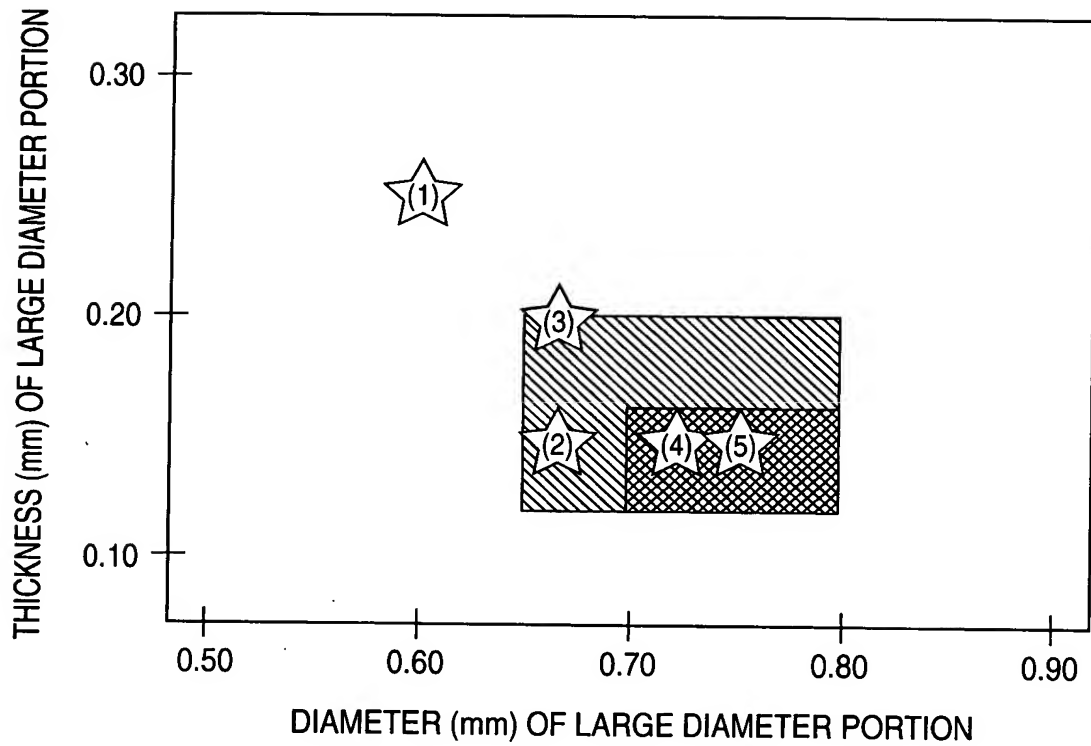


FIG. 7



7/7

FIG. 8

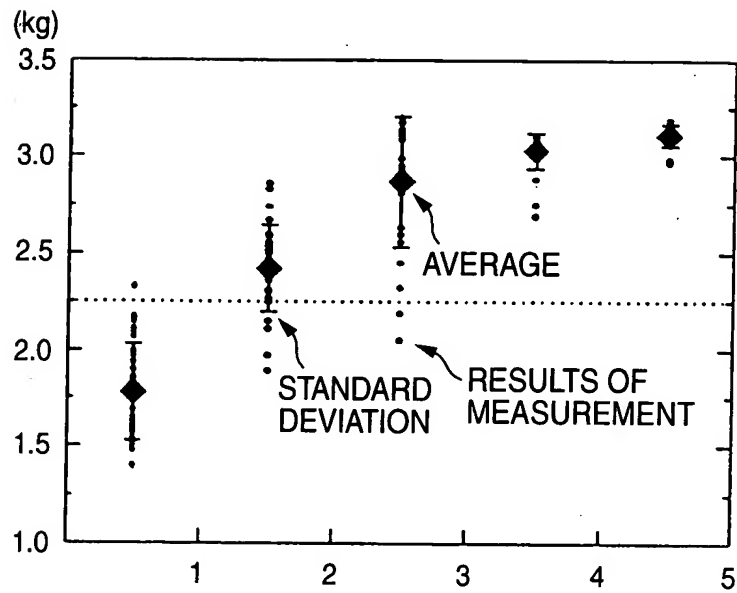


FIG. 9

